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ISL9V2040D3S / ISL9V2040S3S / ISL9V2040P3

EcoSPARK[®] 200mJ, 400V, N-Channel Ignition IGBT

General Description

The ISL9V2040D3S, ISL9V2040S3S, and ISL9V2040P3 are the next generation ignition IGBTs that offer outstanding SCIS capability in the space saving D-Pak (TO-252), as well as the industry standard D²-Pak (TO-263) and TO-220 plastic packages. This device is intended for use in automotive ignition circuits, specifically as a coil driver. Internal diodes provide voltage clamping without the need for external components.

EcoSPARK¤ devices can be custom made to specific clamp voltages. Contact your nearest Fairchild sales office for more information.

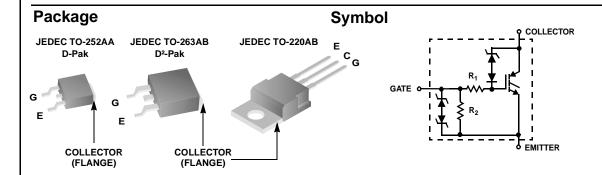
Formerly Developmental Type 49444

Applications

- · Automotive Ignition Coil Driver Circuits
- Coil- On Plug Applications

Features

- · Space saving D Pak package available
- SCIS Energy = 200mJ at T_J = 25°C
- Logic Level Gate Drive



Device Maximum Ratings T_A = 25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
BV _{CER}	Collector to Emitter Breakdown Voltage (I _C = 1 mA)	430	V
BV _{ECS}	Emitter to Collector Voltage - Reverse Battery Condition (I _C = 10 mA)	24	V
E _{SCIS25}	At Starting $T_J = 25$ °C, $I_{SCIS} = 11.5A$, $L = 3.0$ mHy	200	mJ
E _{SCIS150}	At Starting T _J = 150°C, I _{SCIS} = 8.9A, L = 3.0mHy	120	mJ
I _{C25}	Collector Current Continuous, At T _C = 25°C, See Fig 9	10	Α
I _{C110}	Collector Current Continuous, At T _C = 110°C, See Fig 9	10	Α
V _{GEM}	Gate to Emitter Voltage Continuous	±10	V
P _D	Power Dissipation Total T _C = 25°C	130	W
	Power Dissipation Derating T _C > 25°C	0.87	W/°C
TJ	Operating Junction Temperature Range	-40 to 175	°C
T _{STG}	Storage Junction Temperature Range	-40 to 175	°C
TL	Max Lead Temp for Soldering (Leads at 1.6mm from Case for 10s)	300	°C
T _{pkq}	Max Lead Temp for Soldering (Package Body for 10s)	260	°C
ESD	Electrostatic Discharge Voltage at 100pF, 1500Ω	4	kV

		ng and Orderin								
Device N		Device	Package		Reel Size	Та	Tape Width		Quantity	
V2040D		ISL9V2040D3ST	TC)-252AA	330mm		16mm	2500		
V2040S ISL9V2040S3ST T		TC)-263AB	330mm		24mm		800		
V2040P ISL9V2040P3		TC	TO-220AB Tube		N/A			50		
V2040D		ISL9V2040D3S	TO-252AA		Tube	N/A			75	
V2040S ISL9V2040S3S TO)-263AB	Tube		N/A		50		
Electric	al Char	racteristics T _A = 2	5°C un	less otherwise	noted					
Symbol		Parameter		Test Conditions		Min	Тур	Max	Units	
Off State	Charact	eristics								
BV _{CER}	Collector to Emitter Breakdown Voltage			I_C = 2mA, V_{GE} = 0, R_G = 1K Ω , See Fig. 15 T_J = -40 to 150°C		370	400	430	V	
BV _{CES}	Collector	llector to Emitter Breakdown Voltage		$I_C = 10$ mA, $V_{GE} = 0$, $R_G = 0$, See Fig. 15 $T_J = -40$ to 150°C		390	420	450	V	
BV _{ECS}	Emitter to	Collector Breakdown Vo	oltage	I _C = -75mA, \ T _C = 25°C	$V_{GE} = 0V$,	30	-	-	V	
BV_{GES}	Gate to E	mitter Breakdown Voltag	je	$I_{GES} = \pm 2mA$	١	±12	±14	-	V	
I _{CER}	Collector	to Emitter Leakage Curr	ent	V _{CER} = 250V		-	-	25	μΑ	
				$R_G = 1K\Omega$, See Fig. 11	T _C = 150°C	-	-	1	mA	
I _{ECS}	Emitter to	Collector Leakage Curr	ent		$T_C = 25^{\circ}C$	-	-	1	mA	
				Fig. 11	$T_C = 150$ °C	-	-	40	mA	
R ₁	Series G	Series Gate Resistance				-	70	-	Ω	
R_2	Gate to E	mitter Resistance				10K	-	26K	Ω	
n State	Characte	eristics								
V _{CE(SAT)}	Collector	ctor to Emitter Saturation Voltage		$I_C = 6A,$ $V_{GE} = 4V$	T _C = 25°C, See Fig. 3	-	1.45	1.9	V	
V _{CE(SAT)}	Collector	to Emitter Saturation Voltage		$I_C = 10A,$ $V_{GE} = 4.5V$	T _C = 150°C See Fig. 4	-	1.95	2.3	V	
ynamic	Charact	eristics								
$Q_{G(ON)}$	Gate Cha	arge		I _C = 10A, V _{CE} = 12V, V _{GE} = 5V, See Fig. 14		-	12	-	nC	
V _{GE(TH)}	Gate to E	Emitter Threshold Voltage)	$I_C = 1.0 \text{mA},$	$T_C = 25$ °C	1.3	-	2.2	V	
				$V_{CE} = V_{GE}$, See Fig. 10	T _C = 150°C	0.75	-	1.8	V	
V_{GEP}	Gate to E	Emitter Plateau Voltage		$I_C = 10A, V_{CE} = 12V$		-	3.4	-	V	
witching	g Charac	teristics								
t _{d(ON)R}	Current 7	īurn-On Delay Time-Resi	stive	V _{CE} = 14V, R			0.61	-	μs	
t _{riseR}	Current F	Rise Time-Resistive		$V_{GE} = 5V$, $R_G = 1K\Omega$ $T_J = 25$ °C		-	2.17	-	μs	
t _{d(OFF)L}	Current 7	īurn-Off Delay Time-Indu	ctive	$V_{CE} = 300V, L = 500\mu Hy,$		-	3.64	-	μs	
t _{fL}	Current F	Fall Time-Inductive		$V_{GE} = 5V, R_{G}$ $T_{J} = 25$ °C, Se	-	2.36	-	μs		
SCIS	Self Clan	nped Inductive Switching		$T_J = 25^{\circ}\text{C}, L$ $R_G = 1K\Omega, V$ Fig. 1 & 2	= 3.0mHy, ' _{GE} = 5V, See	-	-	200	mJ	
hermal (Characte	eristics								
$R_{\theta JC}$	Thermal	Resistance Junction-Cas	se	TO-252, TO-2	263, TO-220	-	-	1.15	°C/V	

Typical Performance Curves

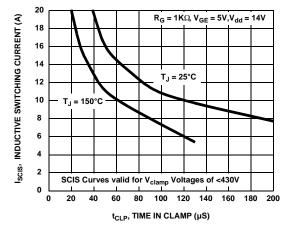


Figure 1. Self Clamped Inductive Switching Current vs Time in Clamp

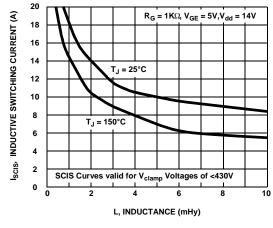


Figure 2. Self Clamped Inductive Switching Current vs Inductance

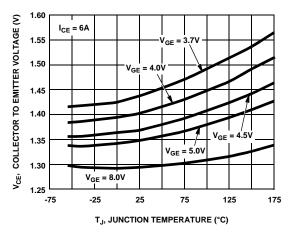


Figure 3. Collector to Emitter On-State Voltage vs Junction Temperature

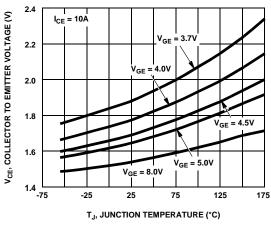


Figure 4. Collector to Emitter On-State Voltage vs Junction Temperature

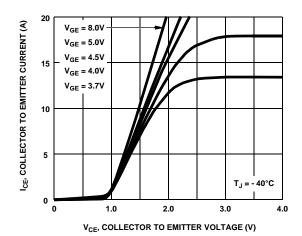


Figure 5. Collector to Emitter On-State Voltage vs Collector Current

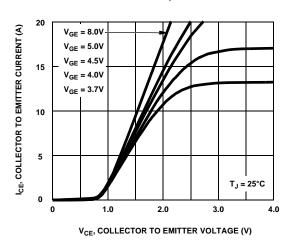
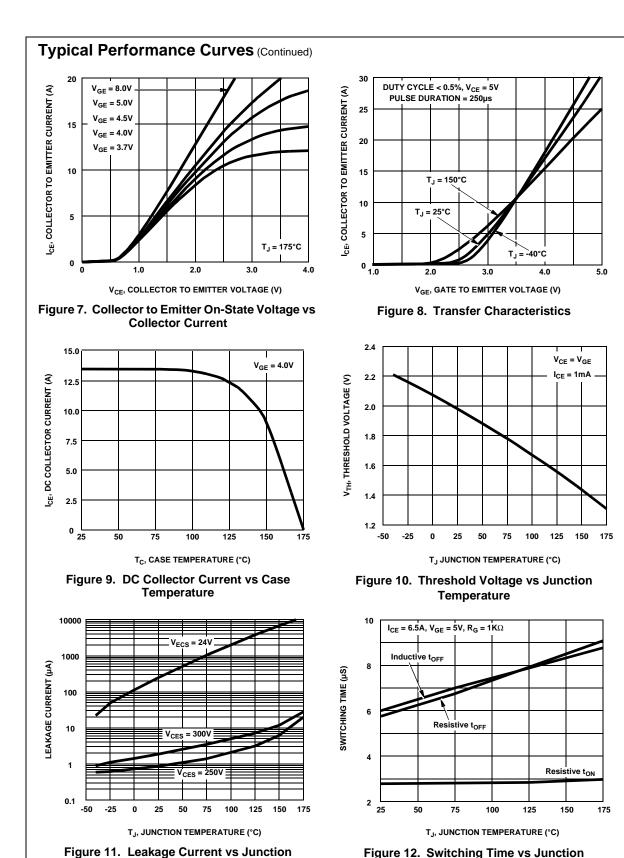


Figure 6. Collector to Emitter On-State Voltage vs Collector Current



Temperature

Temperature

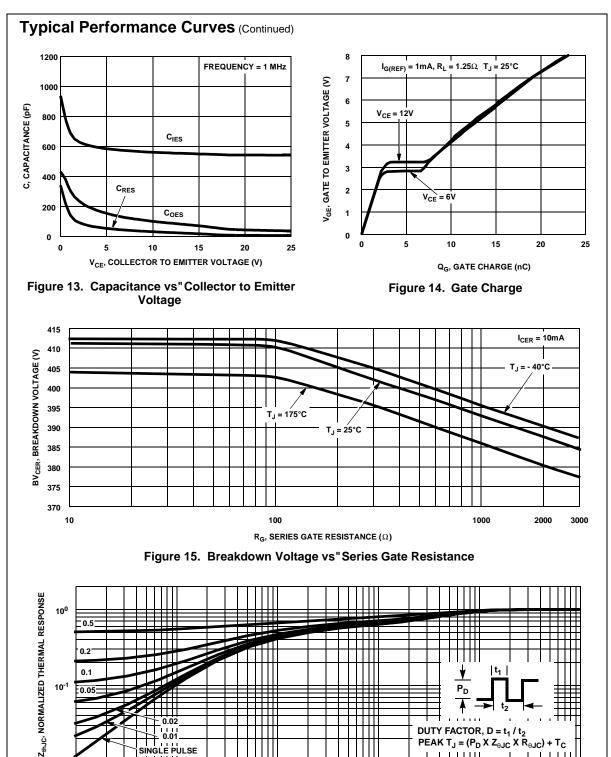


Figure 16. IGBT Normalized Transient Thermal Impedance, Junction to Case

T₁, RECTANGULAR PULSE DURATION (s)

10⁻²

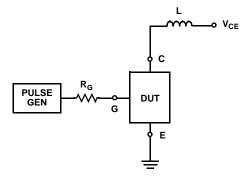
10⁻³

10⁻² 10⁻⁵

10⁻⁴

10⁰

Test Circuit and Waveforms



 $R_{G} = 1K\Omega$ DUT V_{CE}

Figure 17. Inductive Switching Test Circuit

Figure 18. t_{ON} and t_{OFF} Switching Test Circuit

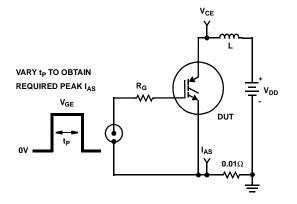


Figure 19. Unclamped Energy Test Circuit

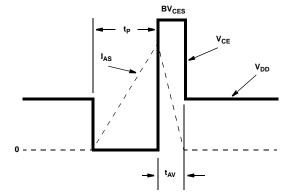


Figure 20. Unclamped Energy Waveforms

SPICE Thermal Model JUNCTION REV 25 April 2002 ISL9V2040D3S, ISL9V2040S3S, ISL9V2040P3 CTHERM1 th 6 1.3e -2 CTHERM2 6 5 8.8e -4 CTHERM3 5 4 8.8e -3 RTHERM1 CTHERM1 CTHERM4 4 3 3.9e -1 CTHERM5 3 2 3.6e -1 CTHERM6 2 tl 1.9e -1 6 RTHERM1 th 6 1.2e -1 RTHERM2 6 5 3.2e -1 RTHERM3 5 4 1.7e -1 RTHERM2 CTHERM2 RTHERM4 4 3 1.2e -1 RTHERM5 3 2 1.3e -1 RTHERM6 2 tl 2.5e -1 5 SABER Thermal Model SABER thermal model ISL9V2040D3S, ISL9V2040S3S, ISL9V2040P3 RTHERM3 CTHERM3 template thermal_model th tl thermal c th, tl ctherm.ctherm1 th 6 = 1.3e - 3ctherm.ctherm2 6 5 = 8.8e - 4ctherm.ctherm354 = 8.8e - 3RTHERM4 CTHERM4 ctherm.ctherm4 43 = 3.9e -1ctherm.ctherm5 32 = 3.6e - 1ctherm.ctherm6 2 tl = 1.9e -1 3 rtherm.rtherm1 th 6 = 1.2e -1rtherm.rtherm2 6 5 = 3.2e - 1rtherm.rtherm354 = 1.7e - 1RTHERM5 CTHERM5 rtherm.rtherm4 4 3 = 1.2e - 1rtherm.rtherm5 32 = 1.3e - 1rtherm.rtherm6 2 tl = 2.5e -1 2 RTHERM6 CTHERM6

CASE





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